

SPEC SHEET (FOR REFERENCE)		SHEET No.		Rev.	Page.	
		G05081A		2	1 of 1	
TYPE:6PT2706N4D**						
CHIP SIZE	0.28 * 0.28mm					
WAFER SIZE	6 inch					
Maximum Ratings(Ta=25°C)						
Characteristics	Symbol	Ratings	Unit			
Drain-Source voltage	V _{DSS}	60	V			
Gate-Source voltage	V _{GSS}	±20	V			
WAFER PROBING SPEC (Ta=25C)						
No	MODE	LIMIT			UNIT	CONDITIONS
		MIN.	Typ	MAX.		
1	IGSS			±10	uA	VGS=±20V, VDS=0V
2	IDSS			1	uA	VDS=60V, VGS=0V
3	BVDSS	60			V	ID=10uA, VGS=0V
4	V _{th}	0.8	1	1.48	V	ID=250uA, VDS=VGS
5	RDS(on)1		3.2	4.2	Ω	ID= 220mA, VGS= 10V
6	RDS(on)2		3.7	4.8	Ω	ID= 220mA, VGS= 4.5V
7	VSD	0.5		1.1	V	IS=115mA, VGS=0V
※Built in ZD between Gate and Source						

PHENITEC SEMICONDUCTOR Corp.